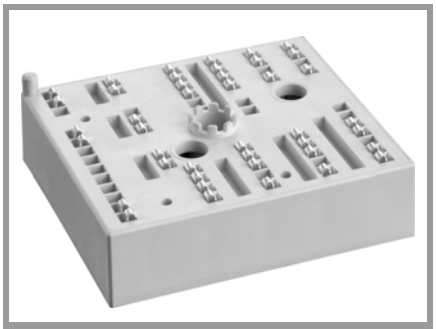
SKiiP 24NAB12T4V1



MiniSKiiP® 2

SKiiP 24NAB12T4V1

Features

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- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

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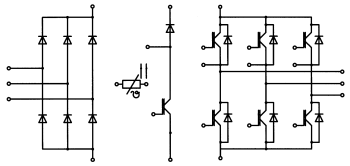
- Inverter up to 22 kVA
- Typical motor power 11 kW

Remarks

- Case temp. limited to T_C = 125°C max. (for baseplateless modules $T_C = T_S$)
- product rel. results valid for $T_j \leq 150$ (recomm. T_{op} = -40 … +150°C)

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Inverter - IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	48	A
	T_j = 175 °C	T_s = 70 °C	39	A
I_C	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	53	A
	T_j = 175 °C	T_s = 70 °C	44	A
I_{Cnom}			35	A
I_{CRM}	I_{CRM} = 3 x I_{Cnom}		105	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 800 V $V_{GE} \leq$ 15 V $V_{CES} \leq$ 1200 V	T_j = 150 °C	10	µs
T_j			-40 ... 175	°C
Chopper - IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	48	A
	T_j = 175 °C	T_s = 70 °C	39	A
I_C	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	53	A
	T_j = 175 °C	T_s = 70 °C	44	A
I_{Cnom}			35	A
I_{CRM}	I_{CRM} = 3 x I_{Cnom}		105	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 800 V $V_{GE} \leq$ 15 V $V_{CES} \leq$ 1200 V	T_j = 150 °C	10	µs
T_j			-40 ... 175	°C
Inverse - Diode				
V_{RRM}	T_j = 25 °C		1200	V
I_F	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	44	A
	T_j = 175 °C	T_s = 70 °C	35	A
I_F	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	49	A
	T_j = 175 °C	T_s = 70 °C	40	A
I_{Fnom}			35	A
I_{FRM}	I_{FRM} = 3 x I_{Fnom}		105	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 150 °C		170	A
T_j			-40 ... 175	°C
Freewheeling - Diode				
V_{RRM}	T_j = 25 °C		1200	V
I_F	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	44	A
	T_j = 175 °C	T_s = 70 °C	35	A
I_F	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	49	A
	T_j = 175 °C	T_s = 70 °C	40	A
I_{Fnom}			35	A
I_{FRM}	I_{FRM} = 3 x I_{Fnom}		105	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 150 °C		170	A
T_j			-40 ... 175	°C



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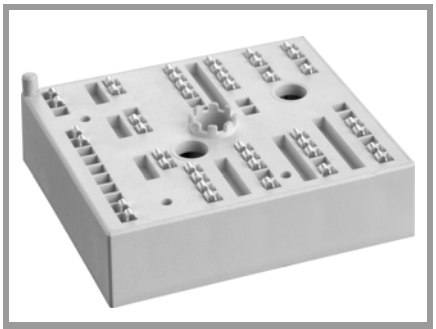
SKiiP 24NAB12T4V1



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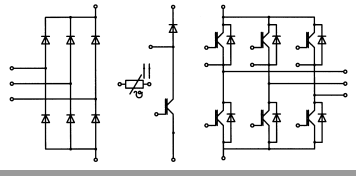
- product rel. results valid for $T_j \leq 150$ (recomm. T_{op} = -40 … +150°C)

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Rectifier - Diode				
V_{RRM}	T_j = 25 °C		1600	V
I_F	λ_{paste}=0.8 W/(mK)	T_s = 25 °C	52	A
	T_j = 150 °C	T_s = 70 °C	39	A
I_F	λ_{paste}=2.5 W/(mK)	T_s = 25 °C	57	A
	T_j = 150 °C	T_s = 70 °C	43	A
I_{Fnom}			13	A
I_{FSM}	10 ms sin 180°	T_j = 25 °C	370	A
		T_j = 150 °C	270	A
I^2t	10 ms sin 180°	T_j = 25 °C	685	A^2s
		T_j = 150 °C	365	A^2s
T_j			-40 ... 150	°C
Module				
$I_{t(RMS)}$	$T_{terminal}$ = 80 °C, 20 A per spring		40	A
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50 Hz, 1 min		2500	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverter - IGBT						
$V_{CE(sat)}$	I_C = 35 A, V_{GE} = 15 V chiplevel	T_j = 25 °C		1.85	2.10	V
		T_j = 150 °C		2.25	2.45	V
V_{CE0}	chiplevel	T_j = 25 °C		0.80	0.90	V
		T_j = 150 °C		0.70	0.80	V
r_{CE}	V_{GE} = 15 V chiplevel	T_j = 25 °C		30	34	mΩ
		T_j = 150 °C		44	47	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}$ V, I_C = 1 mA		5	5.8	6.5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V, T_j = 25 °C			0.1	0.3	mA
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V	f = 1 MHz		1.95		nF
C_{oes}		f = 1 MHz		0.16		nF
C_{res}		f = 1 MHz		0.12		nF
Q_G	V_{GE} = - 8 V...+ 15 V			200		nC
R_{Gint}	T_j = 25 °C			0		Ω
$t_{d(on)}$	V_{CC} = 600 V, I_C = 35 A, $R_{G\,on}$ = 18 Ω, $R_{G\,off}$ = 18 Ω	T_j = 150 °C		30		ns
t_r		T_j = 150 °C		35		ns
E_{on}		T_j = 150 °C		4.3		mJ
$t_{d(off)}$		T_j = 150 °C		300		ns
t_f		T_j = 150 °C		55		ns
E_{off}	V_{GE} = +15/-15 V	T_j = 150 °C		3.25		mJ
$R_{th(j-s)}$	per IGBT, λ_{paste}=0.8 W/(mK)			1		K/W
$R_{th(j-s)}$	per IGBT, λ_{paste}=2.5 W/(mK)			0.82		K/W



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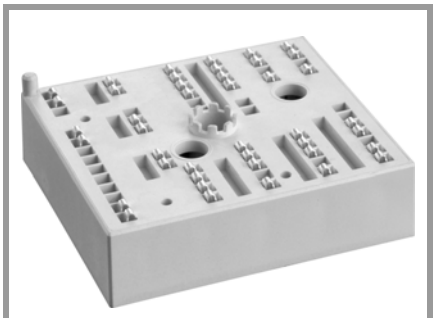

MiniSKiiP® 2

SKiiP 24NAB12T4V1

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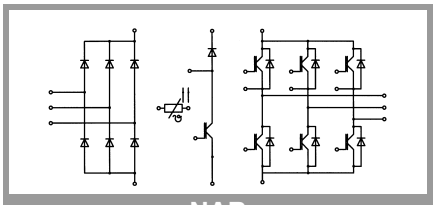
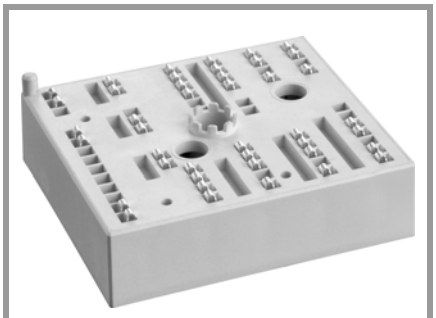


NAB

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Chopper - IGBT						
$V_{CE(sat)}$	I_C = 35 A, V_{GE} = 15 V, chiplevel	T_j = 25 °C		1.85	2.10	V
		T_j = 150 °C		2.25	2.45	V
V_{CE0}	chiplevel	T_j = 25 °C		0.80	0.90	V
		T_j = 150 °C		0.70	0.80	V
r_{CE}	V_{GE} = 15 V, chiplevel	T_j = 25 °C		30	34	mΩ
		T_j = 150 °C		44	47	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}$ V, I_C = 1 mA		5	5.8	6.5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V, T_j = 25 °C			0.1	0.3	mA
Q_G	V_{GE} = - 8 V...+ 15 V			200		nC
R_{Gint}	T_j = 25 °C			0		Ω
$t_{d(on)}$	V_{CC} = 600 V, I_C = 35 A, $R_{G\,on}$ = 18 Ω, $R_{G\,off}$ = 18 Ω	T_j = 150 °C		30		ns
t_r		T_j = 150 °C		35		ns
E_{on}		T_j = 150 °C		4.3		mJ
$t_{d(off)}$		T_j = 150 °C		300		ns
t_f		T_j = 150 °C		55		ns
E_{off}	V_{GE} = +15/-15 V	T_j = 150 °C		3.25		mJ
$R_{th(j-s)}$	per IGBT, λ_{paste}=0.8 W/(mK)			1		K/W
$R_{th(j-s)}$	per IGBT, λ_{paste}=2.5 W/(mK)			0.82		K/W
Inverse - Diode						
$V_F = V_{EC}$	I_F = 35 A, V_{GE} = 0 V, chiplevel	T_j = 25 °C		2.30	2.62	V
		T_j = 150 °C		2.29	2.62	V
V_{F0}	chiplevel	T_j = 25 °C		1.30	1.50	V
		T_j = 150 °C		0.90	1.10	V
r_F	chiplevel	T_j = 25 °C		29	32	mΩ
		T_j = 150 °C		40	43	mΩ
I_{RRM}	I_F = 35 A, di/dt_{off} = 1250 A/µs, V_{GE} = -15 V, V_{CC} = 600 V	T_j = 150 °C		34		A
Q_{rr}		T_j = 150 °C		5.6		µC
E_{rr}		T_j = 150 °C		2.4		mJ
$R_{th(j-s)}$	per Diode, λ_{paste}=0.8 W/(mK)			1.2		K/W
$R_{th(j-s)}$	per Diode, λ_{paste}=2.5 W/(mK)			1		K/W
Freewheeling - Diode						
$V_F = V_{EC}$	I_F = 35 A, V_{GE} = 0 V, chiplevel	T_j = 25 °C		2.30	2.62	V
		T_j = 150 °C		2.29	2.62	V
V_{F0}	chiplevel	T_j = 25 °C		1.30	1.50	V
		T_j = 150 °C		0.90	1.10	V
r_F	chiplevel	T_j = 25 °C		29	32	mΩ
		T_j = 150 °C		40	43	mΩ
I_{RRM}	I_F = 35 A, di/dt_{off} = 1250 A/µs, V_{GE} = -15 V, V_{CC} = 600 V	T_j = 150 °C		34		A
Q_{rr}		T_j = 150 °C		5.6		µC
E_{rr}		T_j = 150 °C		2.4		mJ
$R_{th(j-s)}$	per Diode, λ_{paste}=0.8 W/(mK)			1.2		K/W
$R_{th(j-s)}$	per Diode, λ_{paste}=2.5 W/(mK)			1		K/W



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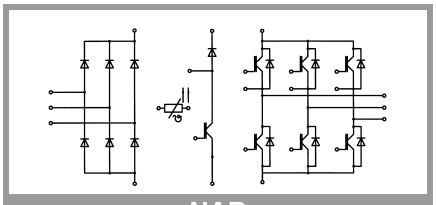
Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Rectifier - Diode						
$V_F = V_{EC}$	I_F = 13 A V_{GE} = 0 V chiplevel	T_j = 25 °C		1.00	1.21	V
		T_j = 125 °C		0.90	1.10	V
V_{F0}	chiplevel	T_j = 25 °C		0.88	0.98	V
		T_j = 125 °C		0.73	0.83	V
r_F	chiplevel	T_j = 25 °C		9.2	18	mΩ
		T_j = 125 °C		13	21	mΩ
$R_{th(j-s)}$	per Diode, λ_{paste}=0.8 W/(mK)			1.25		K/W
$R_{th(j-s)}$	per Diode, λ_{paste}=2.5 W/(mK)			1.1		K/W
Module						
M_s	to heat sink		2		2.5	Nm
w				55		g
L_{CE}				-		nH
Temperature Sensor						
R_{100}	T_r = 100 °C			1670 ± 3%		Ω
R(T)	$R(T)=1000\Omega[1+A(T-25°C)+B(T-25°C)^2]$, $A = 7.635*10^{-3}$ °C^{-1}, $B = 1.731*10^{-5}$ °C^{-2}					



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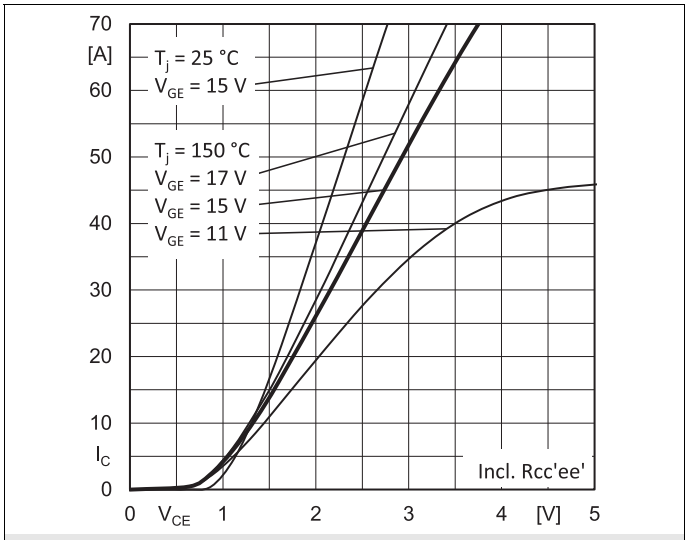


Fig. 1: Typ. output characteristic

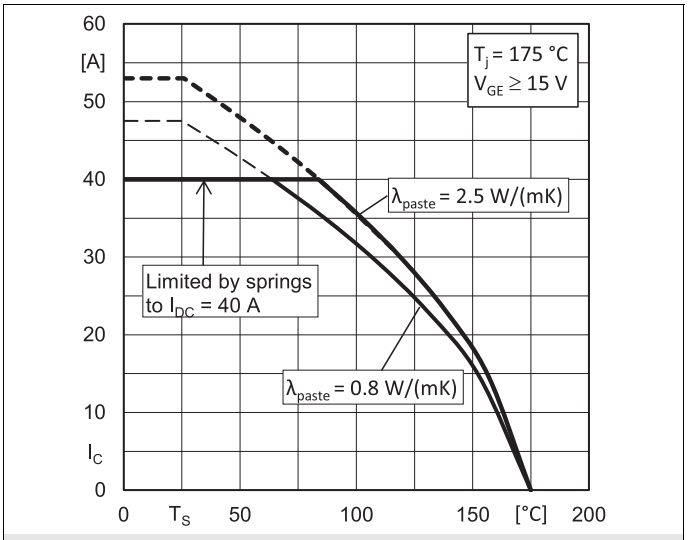


Fig. 2: Typ. rated current vs. temperature $I_C = f(T_S)$

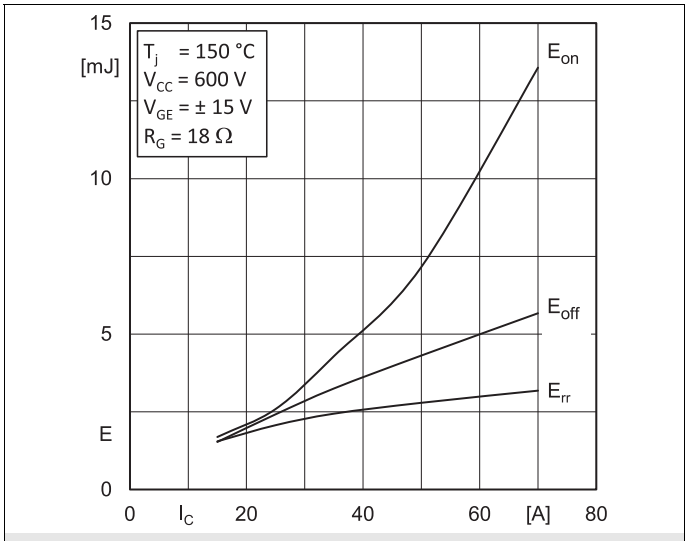


Fig. 3: Typ. turn-on /-off energy = f (I_C)

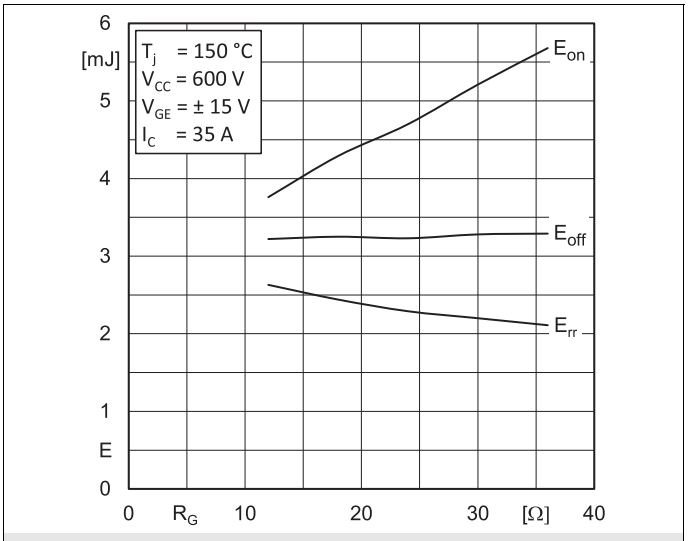


Fig. 4: Typ. turn-on /-off energy = f (R_G)

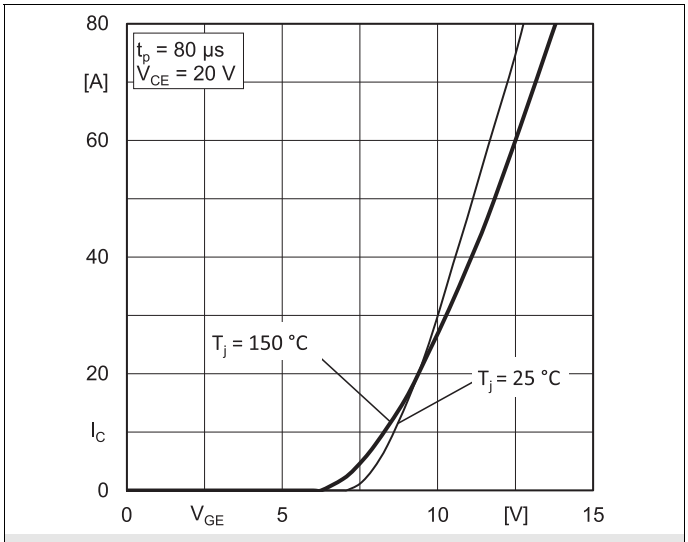


Fig. 5: Typ. transfer characteristic

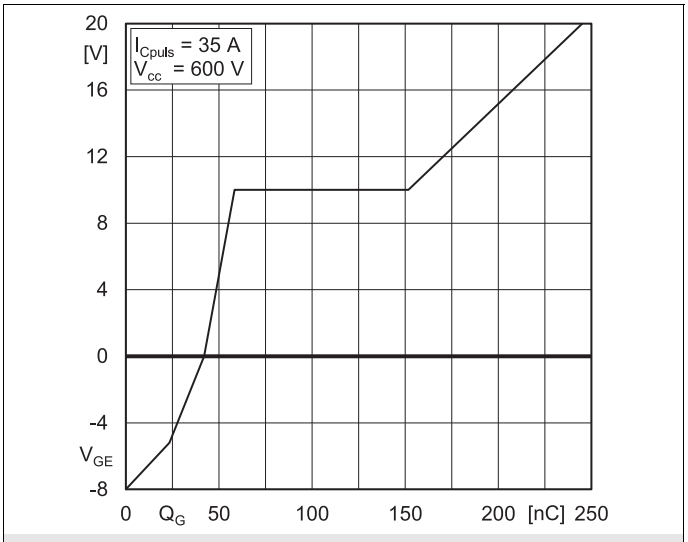


Fig. 6: Typ. gate charge characteristic

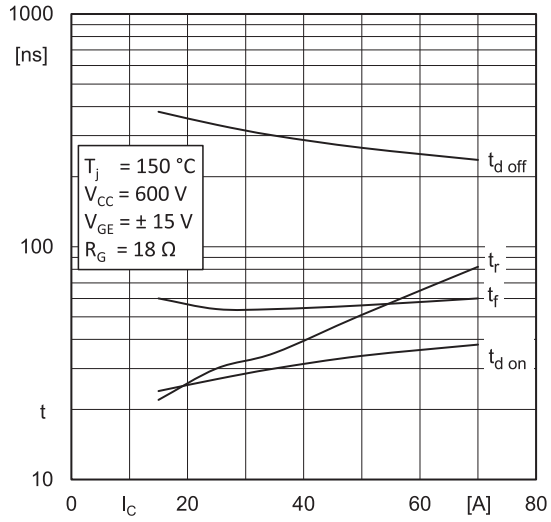


Fig. 7: Typ. switching times vs. I_C

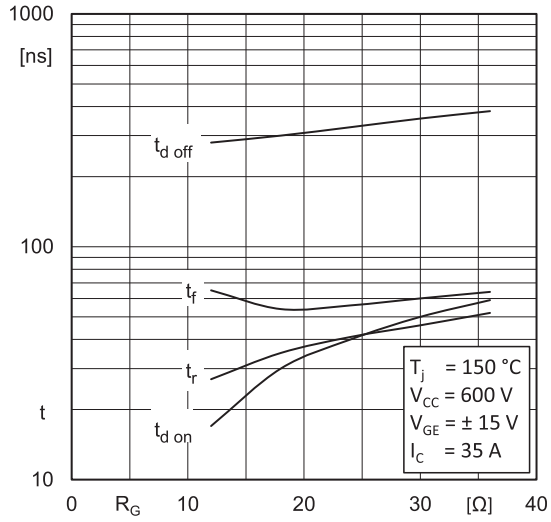


Fig. 8: Typ. switching times vs. gate resistor R_G

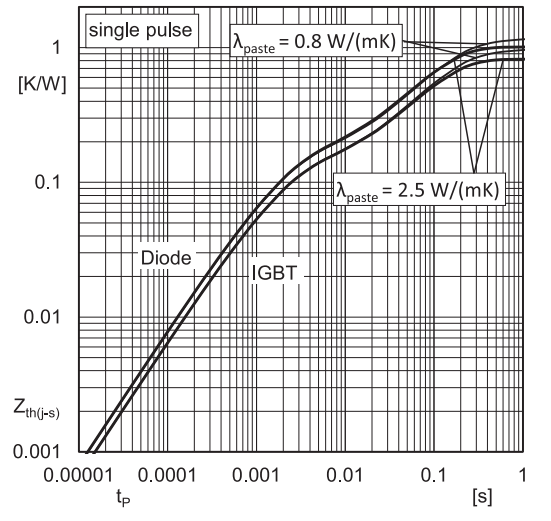


Fig. 9: Transient thermal impedance of IGBT and Diode

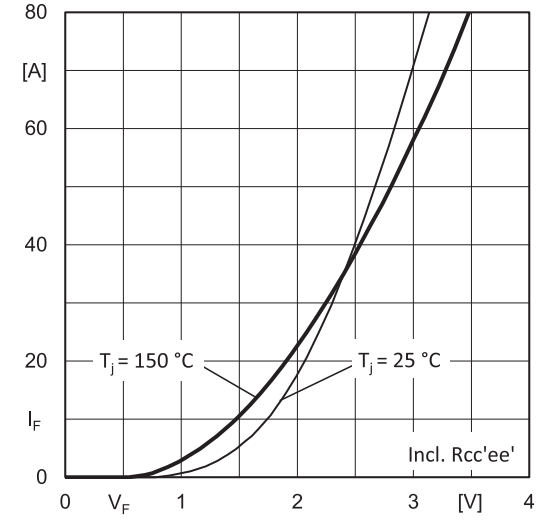


Fig. 10: CAL diode forward characteristic

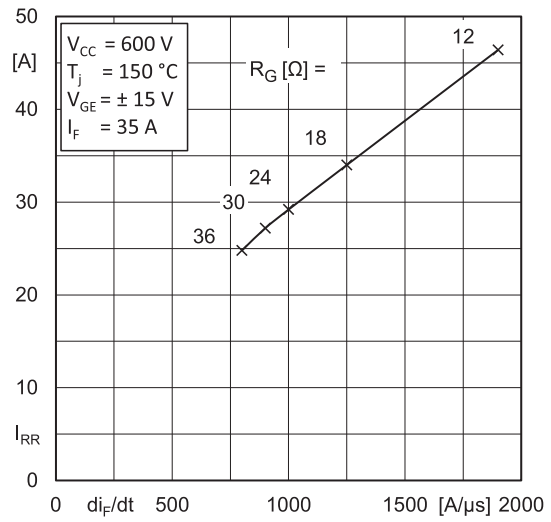


Fig. 11: Typ. CAL diode peak reverse recovery current

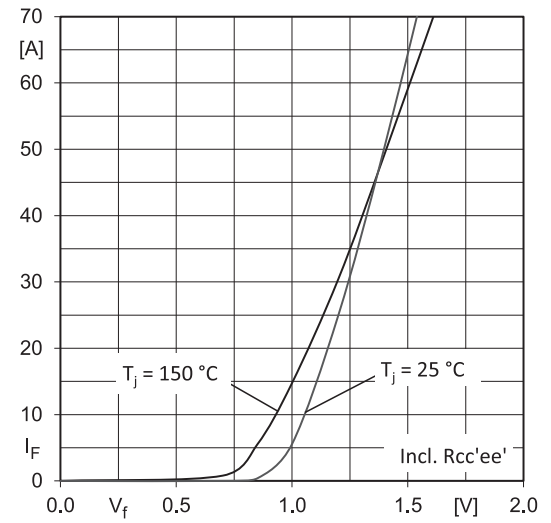
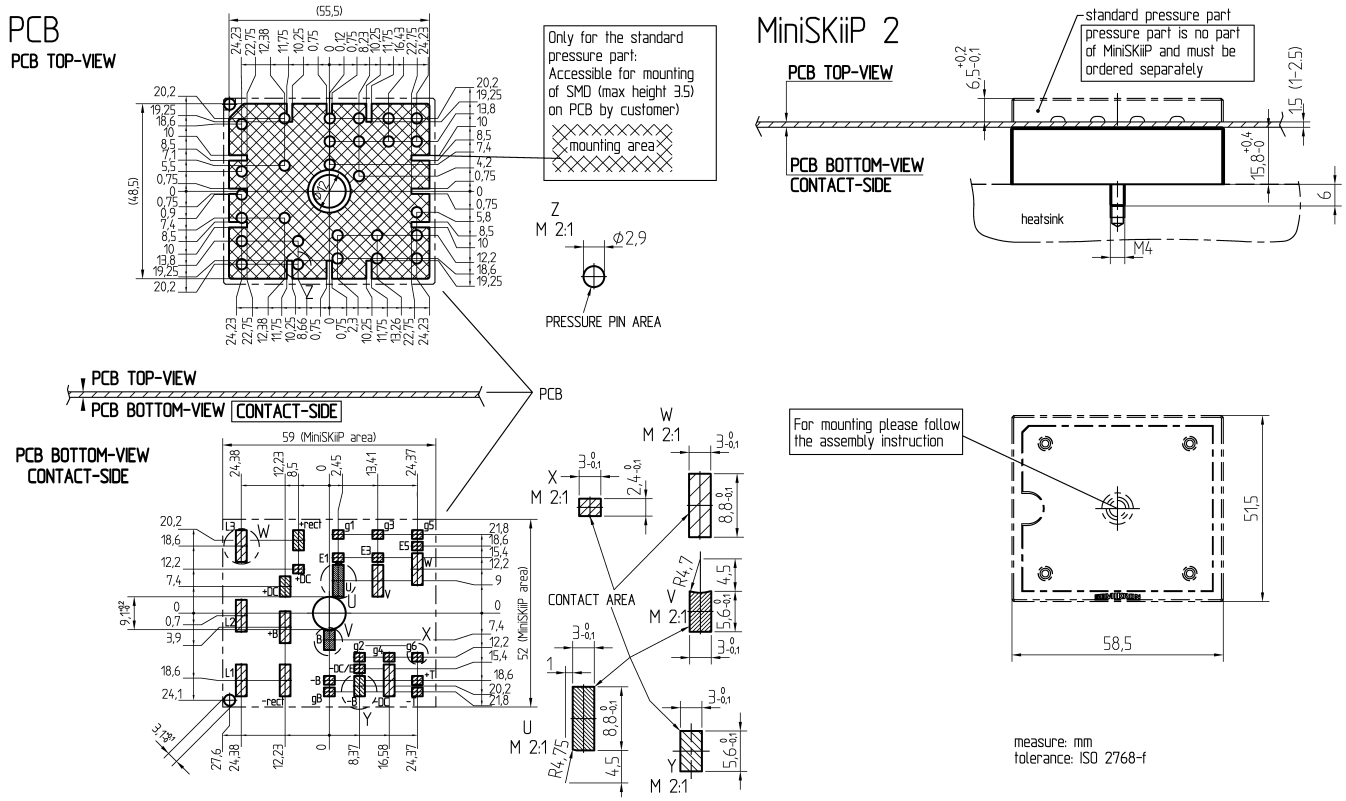
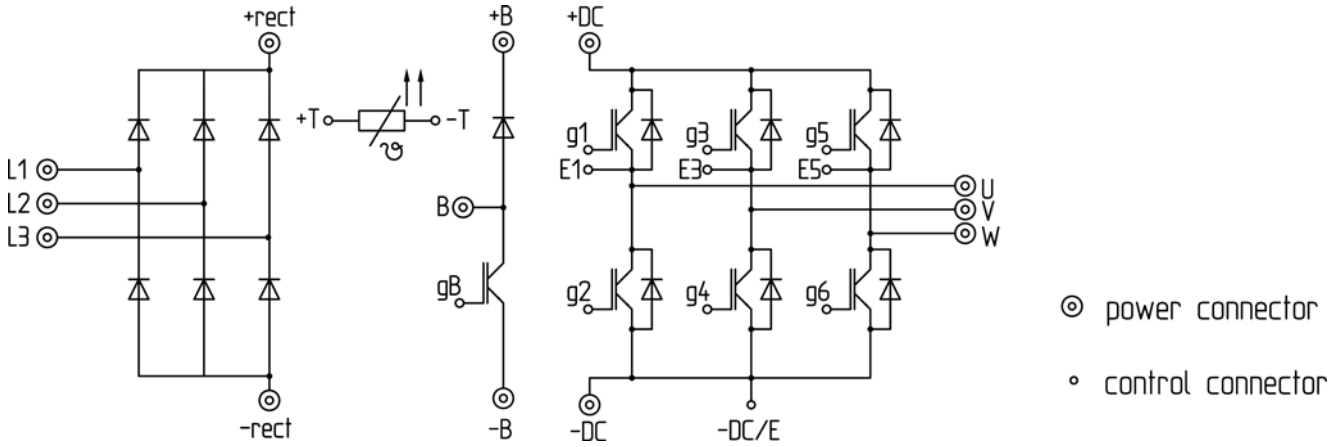


Fig. 12: Typ. input bridge forward characteristic



pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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